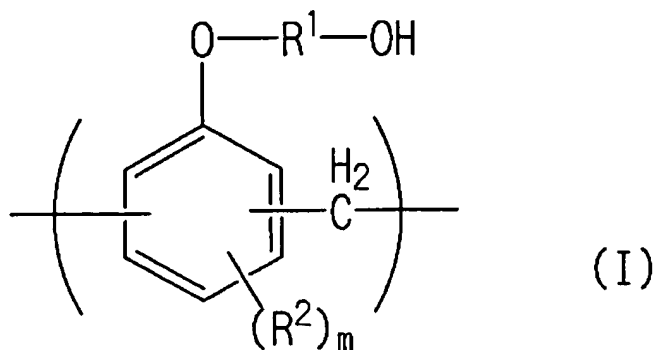


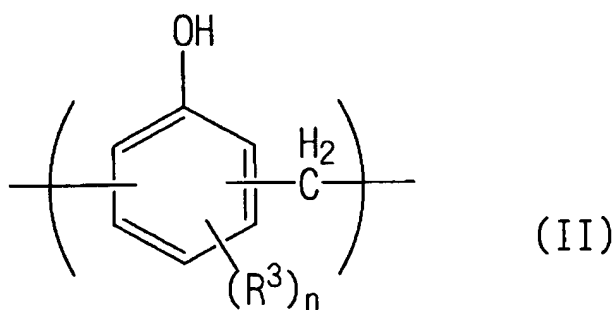
Appl. No. : Unknown  
 Filed : Herewith

### AMENDMENTS TO THE CLAIMS

1. **(Original)** A positive photoresist composition comprising an alkali-soluble novolak resin (A) containing a structural unit (a1) represented by a general formula (I) shown below:



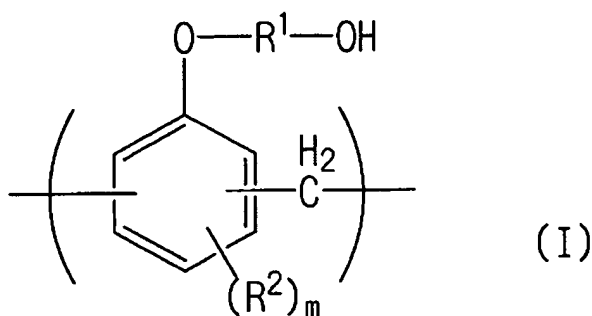
[wherein,  $\text{R}^1$  represents an alkylene group of 1 to 5 carbon atoms,  $\text{R}^2$  represents a hydrogen atom, a hydroxyl group, or an alkyl group of 1 to 4 carbon atoms, and  $m$  represents an integer of 1 to 3], and a structural unit (a2) represented by a general formula (II) shown below:



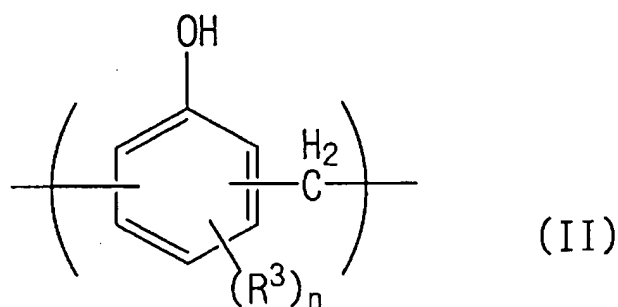
[wherein,  $\text{R}^3$  represents a hydrogen atom, a hydroxyl group, or an alkyl group of 1 to 4 carbon atoms, and  $n$  represents an integer of 1 to 3], and a photosensitizer (B).

Appl. No. : Unknown  
 Filed : Herewith

2. **(Original)** A positive photoresist composition comprising an alkali-soluble novolak resin (A') containing a structural unit (a1) represented by a general formula (I) shown below:



[wherein,  $\text{R}^1$  represents an alkylene group of 1 to 5 carbon atoms,  $\text{R}^2$  represents a hydrogen atom, a hydroxyl group, or an alkyl group of 1 to 4 carbon atoms, and  $m$  represents an integer of 1 to 3], and a structural unit (a2) represented by a general formula (II) shown below:



[wherein,  $\text{R}^3$  represents a hydrogen atom, a hydroxyl group, or an alkyl group of 1 to 4 carbon atoms, and  $n$  represents an integer of 1 to 3], wherein a portion of hydrogen atoms of said hydroxyl groups contained within said resin are substituted with 1,2-naphthoquinonediazidesulfonyl groups.

**Appl. No.** : **Unknown**  
**Filed** : **Herewith**

3. **(Original)** A positive photoresist composition according to claim 2, further comprising a photosensitizer (B).

4. **(Currently Amended)** A method of forming a resist pattern comprising the steps of applying a positive photoresist composition according to ~~any one of claim 1 through~~ claim 3 to a substrate, conducting a prebake, performing selective exposure, and then performing alkali developing to form the resist pattern.